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ABSTRACT OF THE DISCLOSURE

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5 A semiconductor integrated circuit capacitor is provided which includes an insulating substrate and a lower electrode disposed on a predetermined part of the insulating substrate. The capacitor also includes an interlevel insulating layer disposed on the insulating substrate and on the lower electrode, and a via hole having sidewalls, whereby the via hole passes through the interlevel insulating layer and exposes a predetermined surface of the lower electrode. The capacitor also includes a spacer disposed on the sidewalls of the via hole, and a dielectric layer disposed on: (i) a bottom surface of the via hole adjacent to the predetermined surface of the lower electrode; (ii) a predetermined part of the insulating layer; and (iii) the spacer. The capacitor also includes an upper electrode disposed on a predetermined part of the interlevel insulating layer and disposed on the dielectric layer. A method of making the semiconductor integrated circuit capacitor also is disclosed.

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